

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In application of: RAMINDA U. MADURawe
Application No.:
Title: Insulated-Gate Field-Effect Thin Film Transistors
Filed: 01/20/2004

INFORMATION DISCLOSURE STATEMENT SUBMISSION

Sirs:

Attached is IDS form 1449 for the Application submitted herewith entitled "Insulated-Gate Field-Effect Thin Film Transistors", said application a division of Application Serial No 10/413,808 filed on Apr. 14, 2003, copies of said IDS references filed on Jul 31, 2003.

Regards,



Raminda U. Madurawe


CERTIFICATE OF MAILING

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PTO/SB/08A (08-00)

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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 2

Complete if Known

Application Number	
Filing Date	01/20/2004
First Named Inventor	Madurawe, Raminda U.
Group Art Unit	
Examiner Name	
Attorney Docket Number	

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
		4,065,781		Gutknecht	12-27-1977	
		4,502,204		Togashi et al.	03-05-1985	
		5,266,515		Robb et al.	11-30-1993	
		5,340,999		Takeda et al.	08-23-1994	
		5,537,078		Strong	07-16-1996	
		5,656,844		Klein et al.	08-12-1997	
		5,981,317		French et al.	11-09-1999	
		6,107,642		Sundaresan	08-22-2000	
		6,222,234		Imai	04-24-2001	
		6,271,063		Chan et al.	08-07-2001	
		2001/0041399		Bonart	11-15-2001	
		6,380,009		Battersby	04-30-2002	
		6,406,951		Yu	06-18-2002	
		2002/0168804		Van der Zaag et al.	11-14-2002	
		6,545,319		Deane et al.	04-08-2003	
		2002/0079496		Deane et al.	06-27-2002	
		6,579,750		Krivokapic	06-17-2003	
		6,339,244		Krivokapic	01-15-2002	

FOREIGN PATENT DOCUMENTS

Examiner Initials *	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
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